

MTM131270BBF

Silicon P-channel MOS FET

For switching

■ Features

- Low Drain-source On-state Resistance : $R_{DS(on)}$ typ = 92 m Ω (V_{GS} = -4.0 V)
- Low drive voltage: 1.8 V drive
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : EU

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

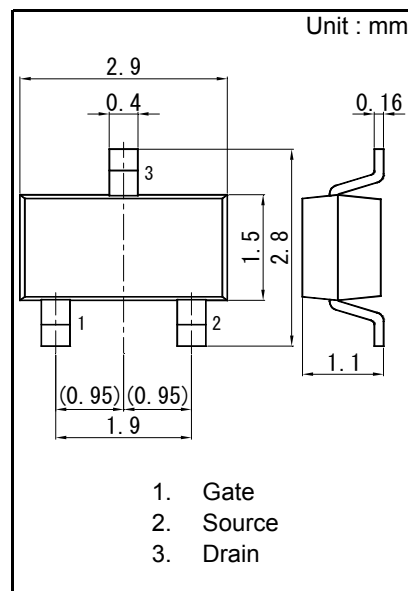
■ Absolute Maximum Ratings T_a = 25 °C

項目	記号	定格	単位
Drain-source Voltage	VDS	-20	V
Gate-source Voltage	VGS	±10	
Drain current	ID	-2	A
Peak drain current ^{*1}	IDp	-8	A
Power dissipation ^{*2}	PD	700	mW
Channel temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note *1 Pulse width $\leq$ 10 μ s, Duty cycle $\leq$ 1 %

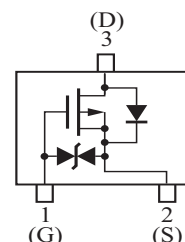
*2 Measuring on ceramic board at 40 × 38 × 0.1 mm.

Absolute maximum rating PD without heat sink shall be made 200 mW.



Panasonic	Mini3-G3-B
JEITA	SC-59A
Code	TO-236AA/SOT-23

Internal Connection



Pin Name

1. Gate
2. Source
3. Drain